

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 21, line 13 with the following amended paragraph:

The gate electrodes 133 are in this case made of a heavily-doped polycrystalline silicon film and W silicide. However, the gate electrodes 133 may be made solely ~~solely~~ of polycrystalline silicon or made of other high melting point metals and silicide. The material of the gate electrodes 133 is determined in consideration of electric resistance and heat resistance.